

**Amplifier, Power, 1.2W
5.7-8.5 GHz**

MAAPGM0068-DIE
Rev B
Preliminary Datasheet

Features

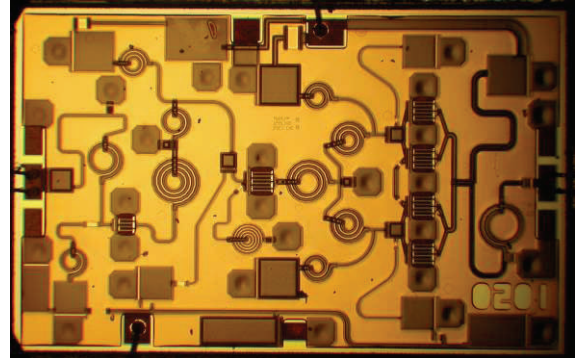
- ◆ 1.5 Watt Saturated Output Power Level
- ◆ Variable Drain Voltage (6-10V) Operation
- ◆ MSAG® Process

Description

The MAAPGM0068-DIE is a 3-stage 1.2W power amplifier with on-chip bias networks. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate (MSAG™) Process, each device is 100% RF tested on wafer to ensure performance compliance.

M/A-COM's MSAG™ process features robust silicon-like manufacturing processes, planar processing of ion implanted transistors, multiple implant capability enabling power, low-noise, switch and digital FETs on a single chip, and polyimide scratch protection for ease of use with automated manufacturing processes. The use of refractory metals and the absence of platinum in the gate metal formulation prevents hydrogen poisoning when employed in hermetic packaging.



Primary Applications

- ◆ Point-to-Point Radio
 - ◇ 6, 7, and 8 GHz Bands
- ◆ SatCom
- ◆ Broadband Wireless Access

Also Available in:

		SAMPLES	
Description	Ceramic	Sample Board (Die)	Mechanical Sample (Die)
Part Number	MAAPGM0068	MAAP-000068-SMB004	MAAP-000068-MCH000

Electrical Characteristics: $T_B = 25^\circ\text{C}^1$, $Z_0 = 50 \Omega$, $V_{DD} = 8\text{V}$, $I_{DQ} = 320 \text{mA}^2$, $P_{in} = 8 \text{dBm}$, $R_G = 300 \Omega$

Parameter	Symbol	Typical	Units
Bandwidth	f	5.7-8.5	GHz
Output Power	P_{OUT}	31	dBm
1-dB Compression Point	P1dB	31	dBm
Small Signal Gain	G	28	dB
Power Added Efficiency	PAE	38	%
Input VSWR	VSWR	1.4:1	
Output VSWR	VSWR	2.1:1	
Output Third Order Intercept	TOI	38	dBm
Output Third Order Intermod, $P_{out} = 24 \text{dBm}$ (DCL)	IMD3	35	dBc
Gate Current	I_{GG}	5	mA
Drain Current	I_{DD}	470	mA

1. T_B = MMIC Base Temperature
2. Adjust V_{GG} between -2.6 and -1.2V to achieve specified I_{dq} .

Maximum Ratings³

Parameter	Symbol	Absolute Maximum	Units
Input Power	P_{IN}	13	dBm
Drain Supply Voltage	V_{DD}	+12.0	V
Gate Supply Voltage	V_{GG}	-3.0	V
Quiescent Drain Current (No RF)	I_{DQ}	520	mA
Quiescent DC Power Dissipated (No RF)	P_{DISS}	5.2	W
Junction Temperature	T_J	170	°C
Storage Temperature	T_{STG}	-55 to +150	°C

3. Operation beyond these limits may result in permanent damage to the part.

Recommended Operating Conditions⁴

Characteristic	Symbol	Min	Typ	Max	Unit
Drain Voltage	V_{DD}	4.0	8.0	10.0	V
Gate Voltage	V_{GG}	-2.6	-2.0	-1.2	V
Input Power	P_{IN}		8.0	11.0	dBm
Thermal Resistance	Θ_{JC}		28.0		°C/W
MMIC Base Temperature	T_B			Note 5	°C

4. Operation outside of these ranges may reduce product reliability.

5. MMIC Base Temperature = 170°C — $\Theta_{JC} * V_{DD} * I_{DQ}$

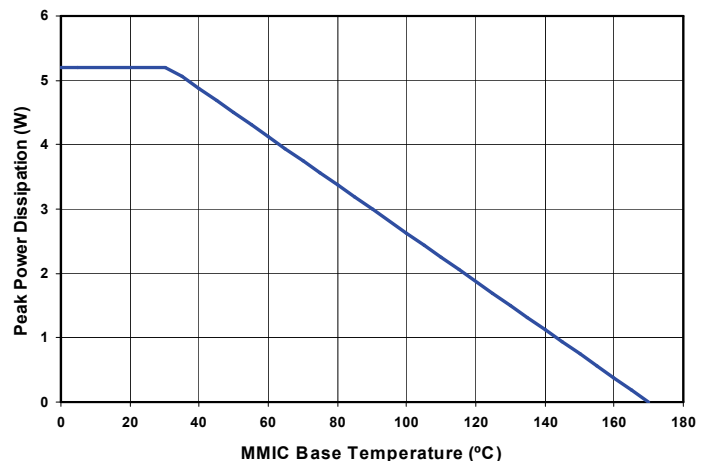


Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply $V_{GG} = -2.7$ V, $V_{DD} = 0$ V.
2. Ramp V_{DD} to desired voltage, typically 8.0 V.
3. Adjust V_{GG} to set I_{DQ} , (approximately @ -2.0 V).
4. Set RF input.
5. Power down sequence in reverse. Turn V_{GG} off last.

Power Derating Curve, Quiescent (No RF)



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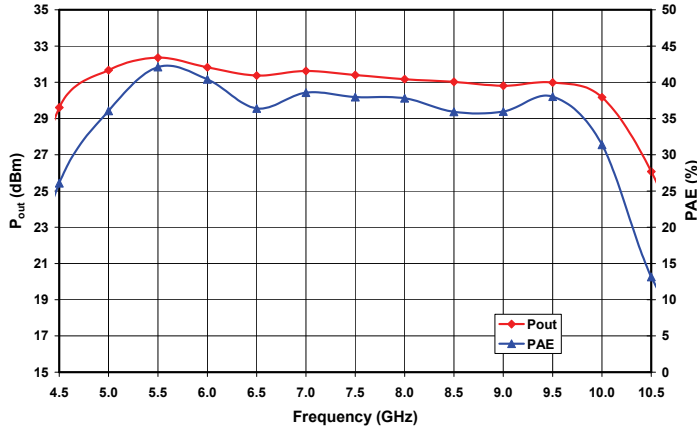


Figure 1. Output Power and Power Added Efficiency at V_D = 8V, P_{in} = 8dBm, and 25% IDSS

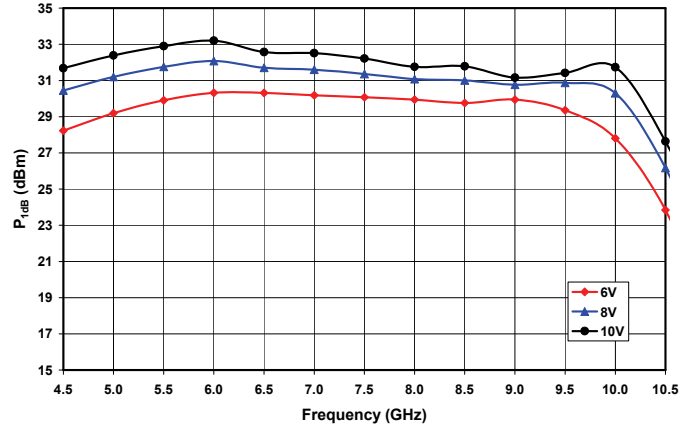


Figure 2. 1dB Compression Point and Drain Voltage at 25% IDSS

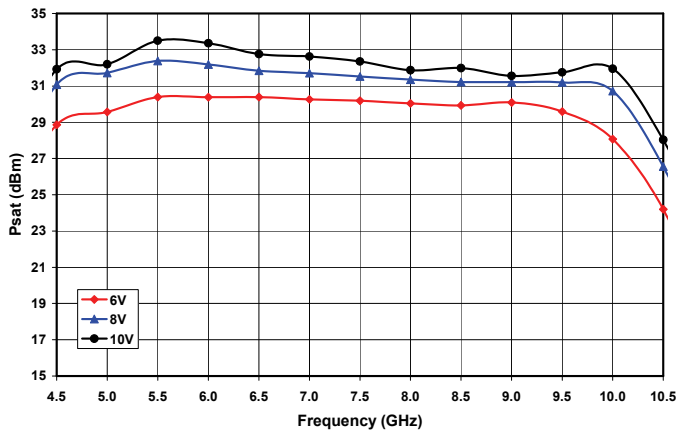


Figure 3. Saturated Output Power and Drain Voltage at 25% IDSS

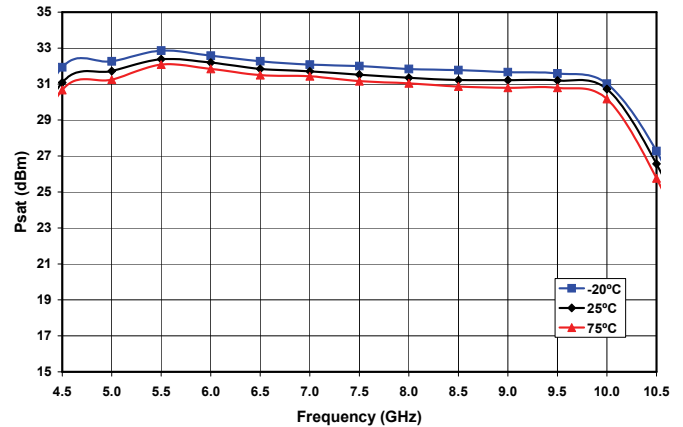


Figure 4. Saturated Output Power and Temperature at 8V and 25% IDSS

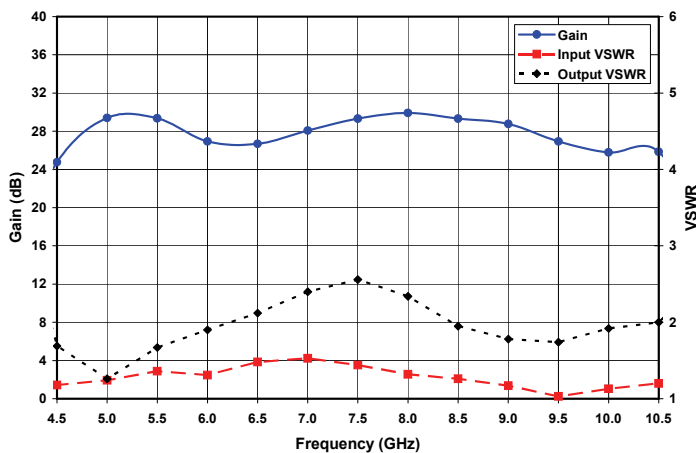


Figure 5. Small Signal Gain and Input and Output VSWR at 25% IDSS and V_D = 8V

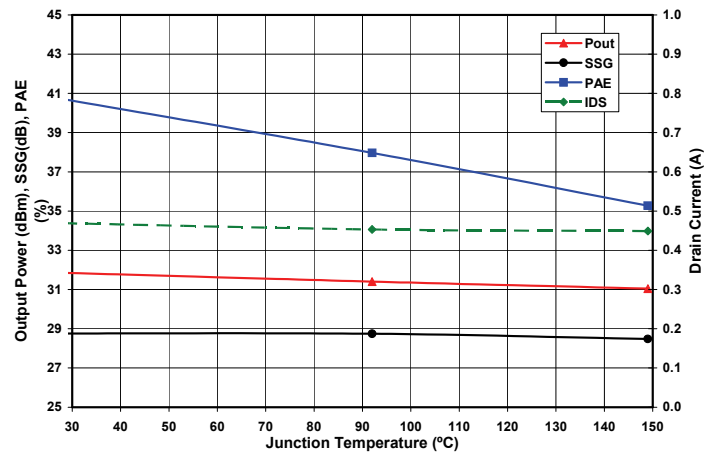


Figure 6. Output Power, Small Signal Gain, Power Added Efficiency, and Drain Current vs. Junction Temperature at 8V, 7.5 GHz, and 25% IDSS

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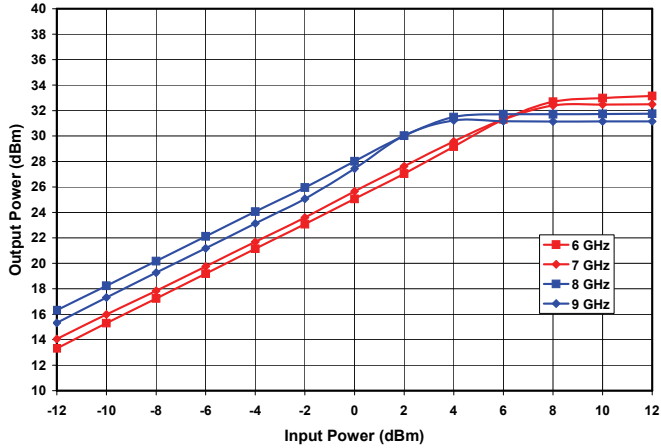


Figure 7. Output Power vs. Input Power and Frequency at 10V and 25% IDSS

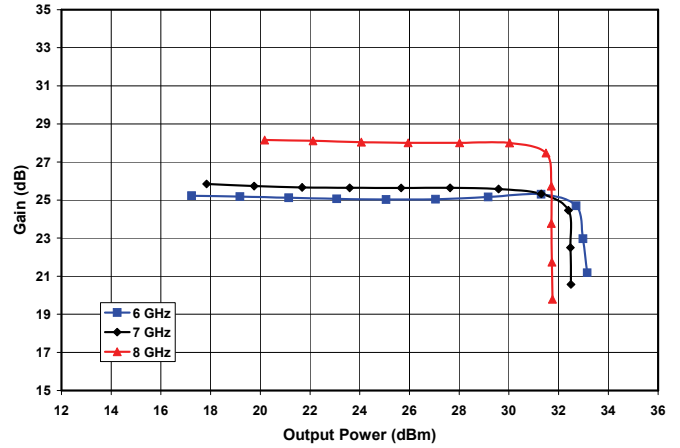


Figure 8. Gain vs. Output Power and Frequency at 10V and 25% IDSS

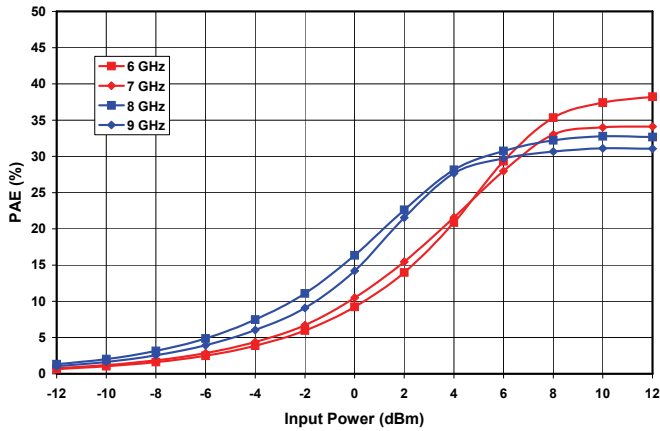


Figure 9. Power Added Efficiency vs. Input Power and Frequency at 10V and 25% IDSS

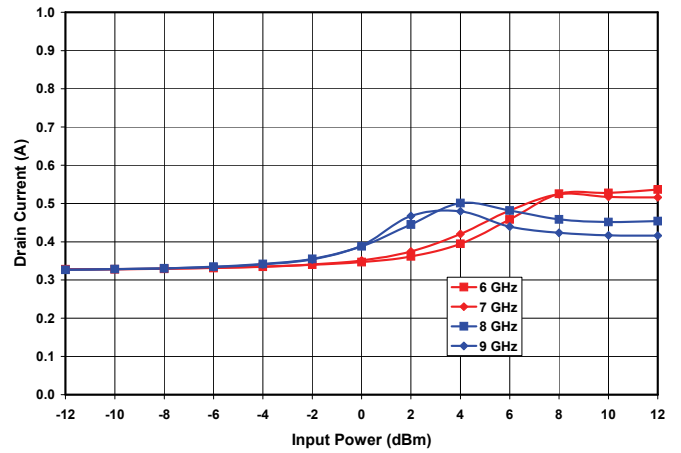


Figure 10. Drain Current vs. Input Power and Frequency at 10V and 25% IDSS

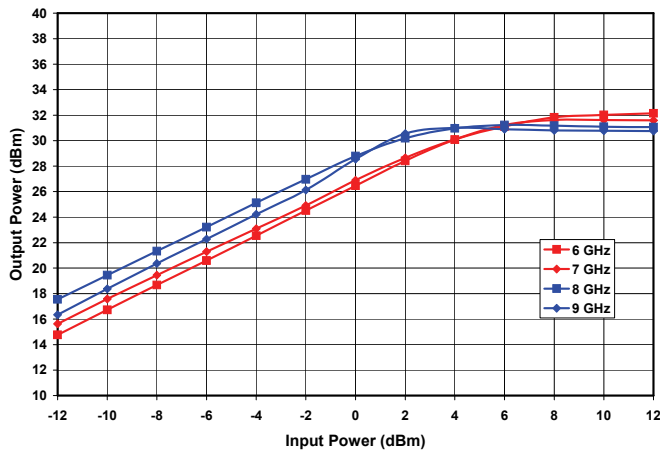


Figure 11. Output Power vs. Input Power and Frequency at 8V and 25% IDSS

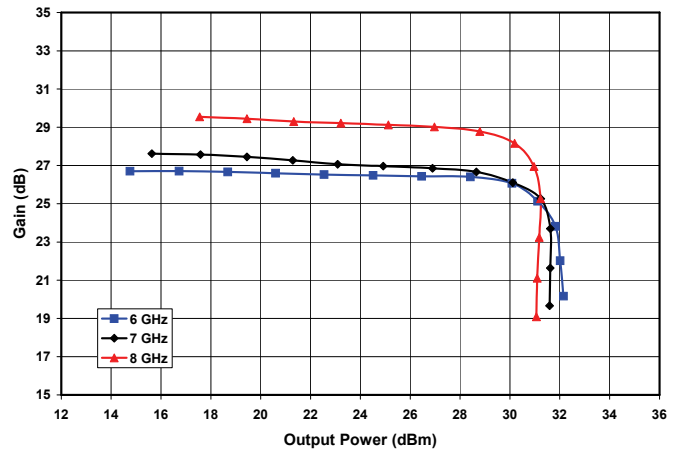


Figure 12. Gain vs. Output Power and Frequency at 8V and 25% IDSS

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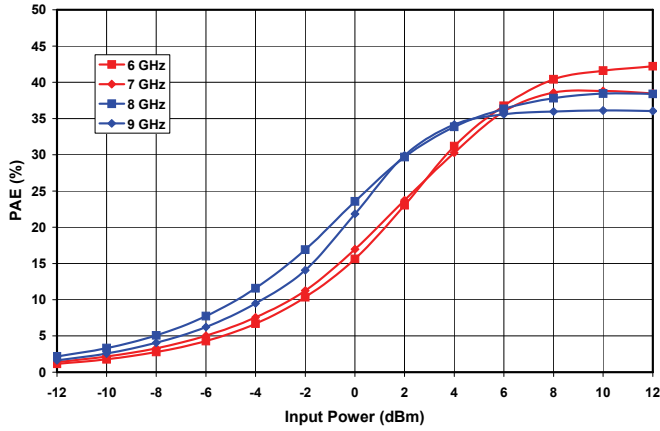


Figure 13. Power Added Efficiency vs. Input Power and Frequency at 8V and 25% IDSS

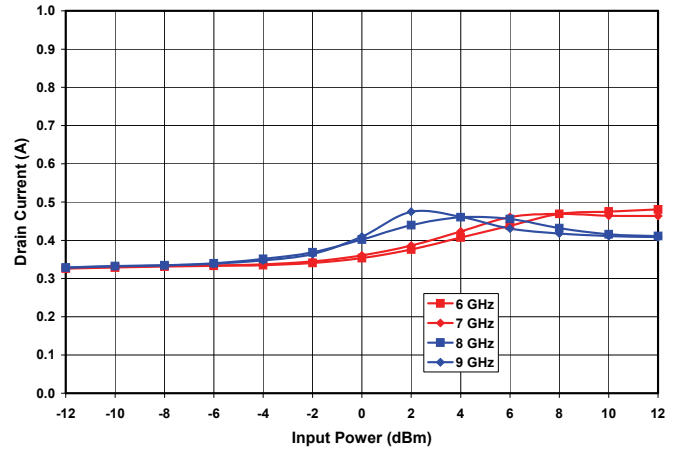


Figure 14. Drain Current vs. Input Power and Frequency at 8V and 25% IDSS

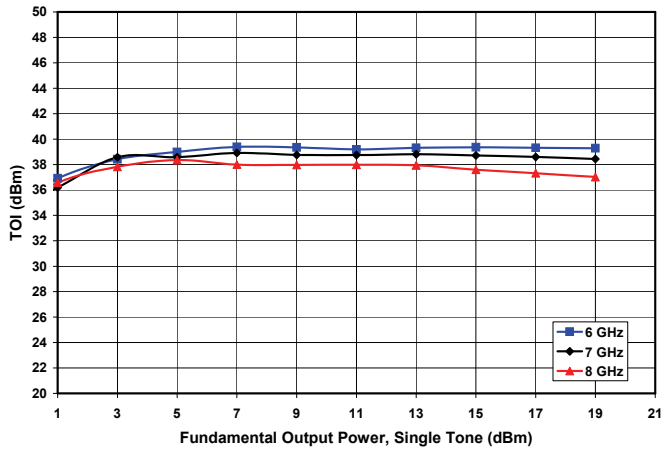


Figure 15. Third Order Intercept vs. Output Power and Frequency at 6V.

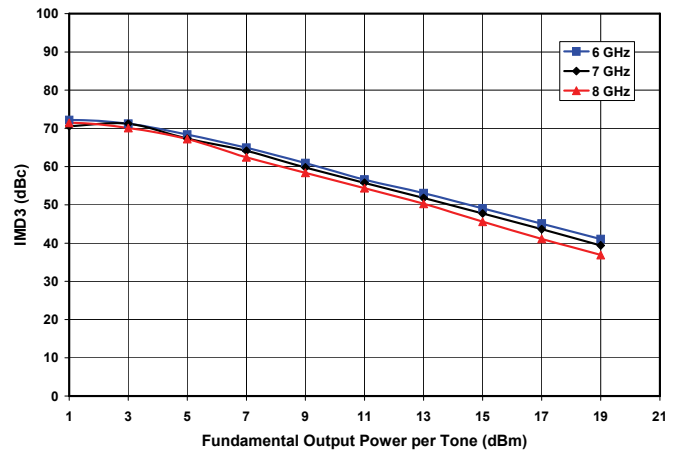


Figure 16. Third Order Intermod vs. Output Power and Frequency at 6V.

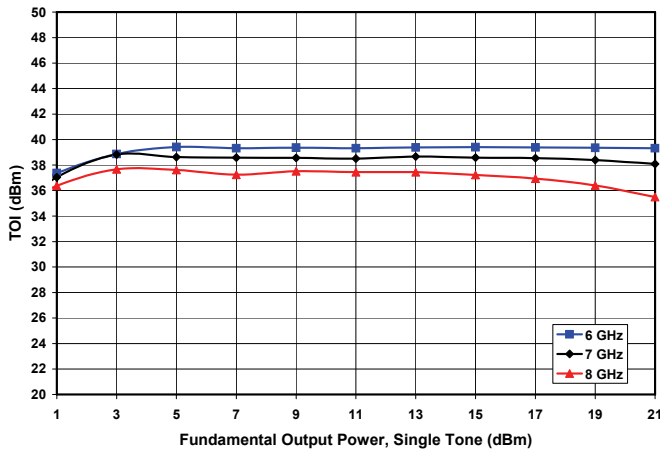


Figure 17. Third Order Intercept vs. Output Power and Frequency at 8V.

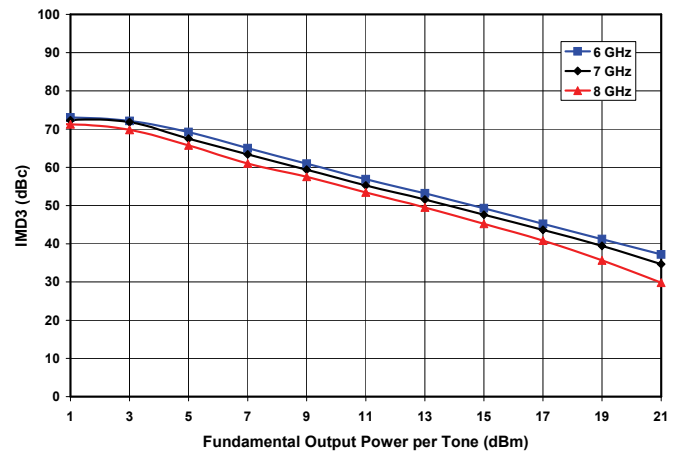


Figure 18. Third Order Intermod vs. Output Power and Frequency at 8V.

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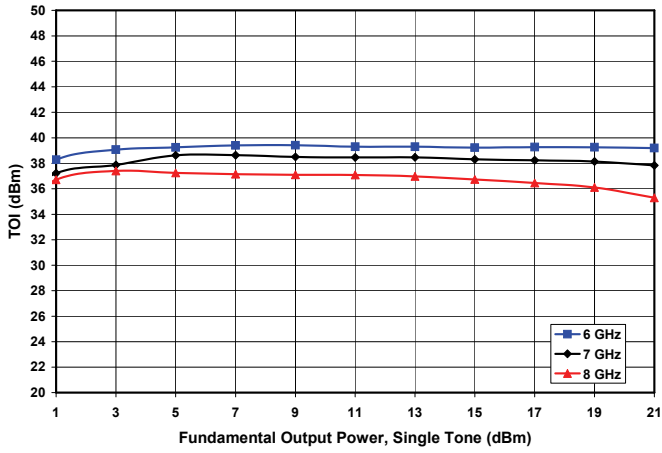


Figure 19. Third Order Intercept vs. Output Power and Frequency at 10V.

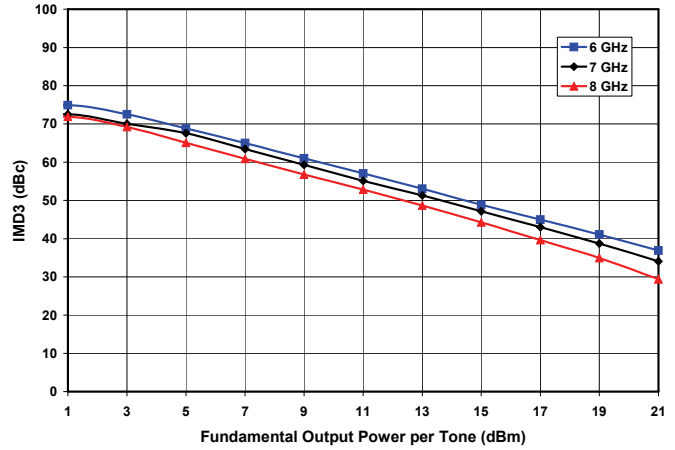


Figure 20. Third Order Intermod vs. Output Power and Frequency at 10V.

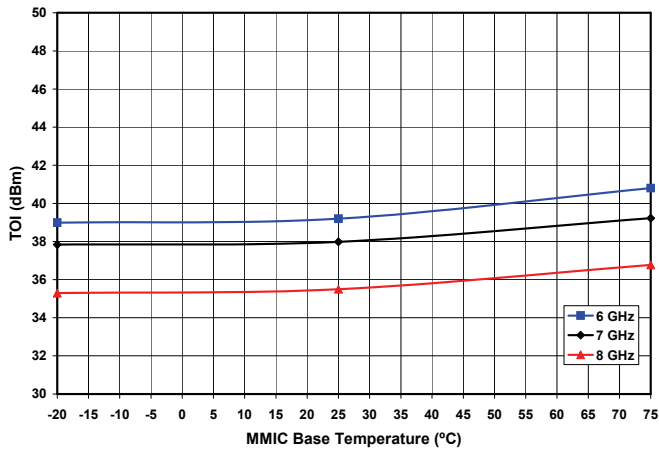


Figure 21. Third Order Intercept vs. Temperature and Frequency at 8V and $P_{out} = 24$ dBm DCL.

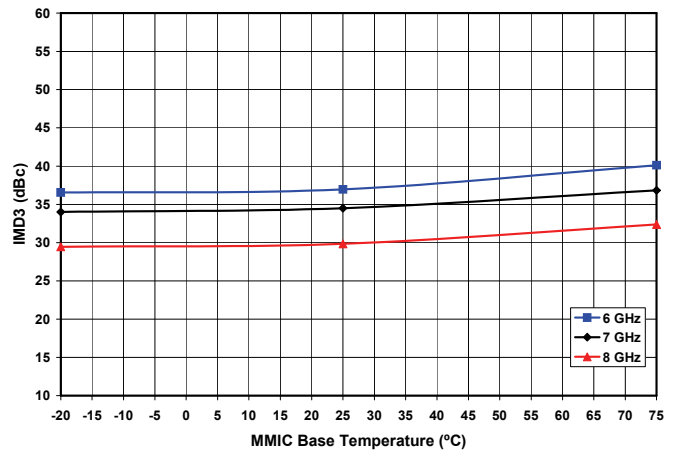
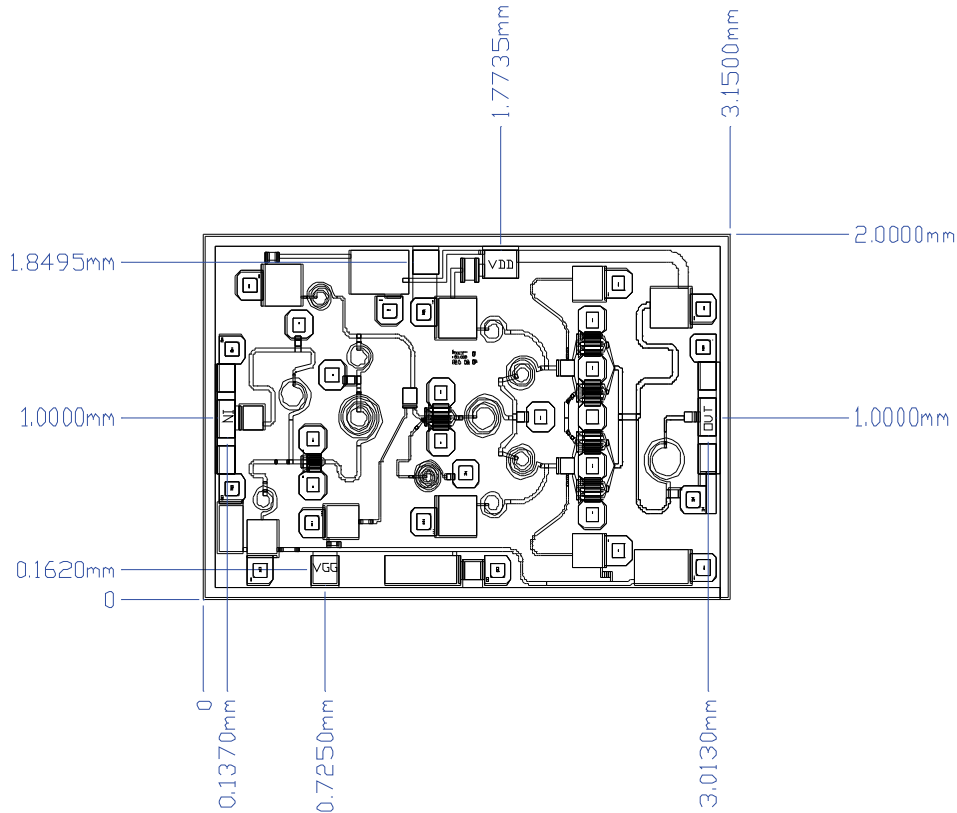


Figure 22. Third Order Intermod vs. Temperature and Frequency at 8V and $P_{out} = 24$ dBm DCL.

Mechanical Information

Chip Size: 2.000 x 3.150 x 0.075 mm (78 x 124 x 3 mils)



Chip edge to bond pad dimensions are shown to the center of the bond pad.

Figure 23. Die Layout

Bond Pad Dimensions

Pad	Size (µm)	Size (mils)
RF In and Out	100 x 200	4 x 8
DC Drain Supply Voltage VDD	200 x 150	8 x 6
DC Gate Supply Voltage VGG	150 x 150	6 x 6

Assembly and Bonding Diagram

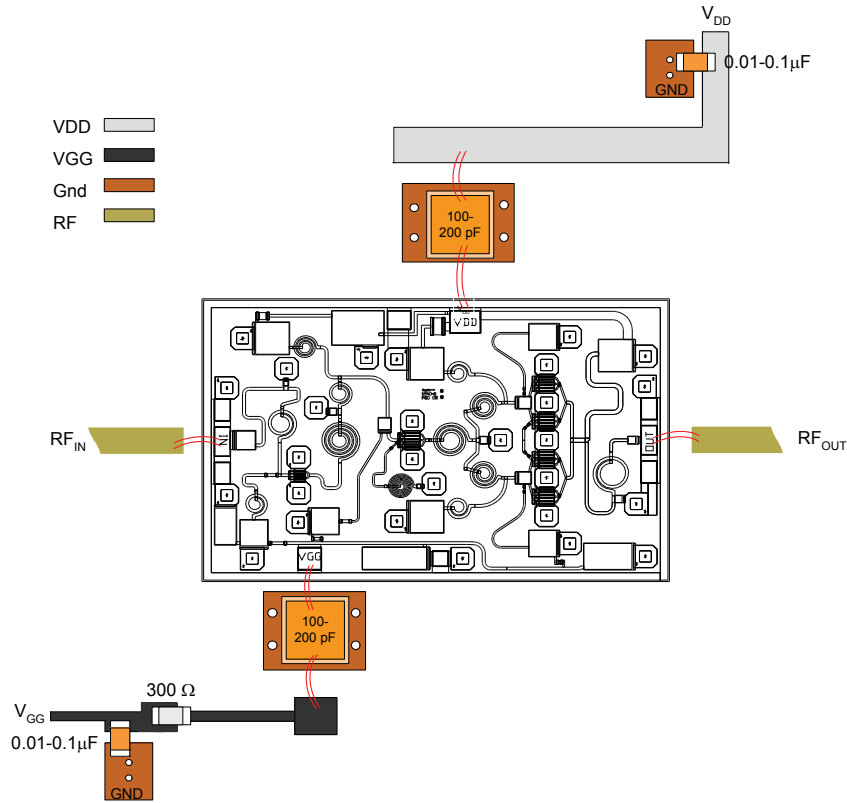


Figure 24. Recommended operational configuration. Wire bond as shown.

Die Handling:

Refer to Application Note AN3016.

Assembly Instructions:

Die Attach: Use AuSn (80/20) 1 mil. preform solder. Limit time @ 310 °C to less than 7 minutes. Refer to Application Note AN3017 for more detailed information.

Wirebonding: Bond @ 160 °C using standard ball or thermal compression wedge bond techniques. For DC pad connections, use either ball or wedge bonds. For best RF performance, use wedge bonds of shortest length, although ball bonds are also acceptable.



Biasing Note: Must apply negative bias to V_{GG} before applying positive bias to V_{DD} to prevent damage to amplifier.